

V_{DSS}	600V
$R_{DS(on)}$ (Max.)	1.2Ω
I_D	6A
P_D	40W

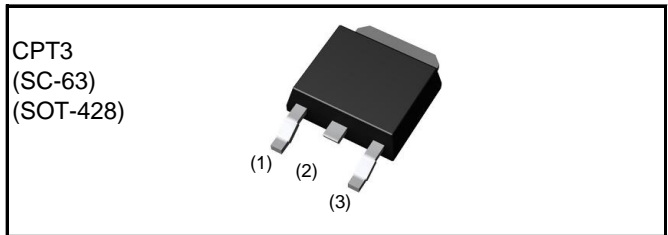
●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be $\pm 30V$.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating ; RoHS compliant

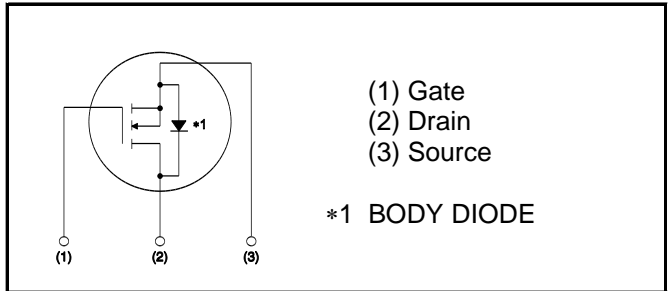
●Application

Switching Power Supply

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	330
	Tape width (mm)	16
	Basic ordering unit (pcs)	2,500
	Taping code	TL
	Marking	R6006A

●Absolute maximum ratings($T_a = 25^\circ C$)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	600	V
Continuous drain current	$T_c = 25^\circ C$	I_D^{*1}	±6 A
	$T_c = 100^\circ C$	I_D^{*1}	±2.9 A
Pulsed drain current	$I_{D,pulse}^{*2}$	±24	A
Gate - Source voltage	V_{GSS}	±30	V
Avalanche energy, single pulse	E_{AS}^{*3}	2.4	mJ
Avalanche energy, repetitive	E_{AR}^{*4}	1.9	mJ
Avalanche current	I_{AR}^{*3}	3	A
Power dissipation ($T_c = 25^\circ C$)	P_D	40	W
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C
Reverse diode dv/dt	dv/dt ^{*5}	15	V/ns

●Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 480V, I_D = 6A$ $T_j = 125^\circ C$	50	V/ns

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R_{thJC}	-	-	3.13	$^\circ C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	100	$^\circ C/W$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^\circ C$

●Electrical characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	600	-	-	V
Drain - Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS} = 0V, I_D = 3A$	-	700	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$ $T_j = 25^\circ C$	-	0.1	100	μA
		$T_j = 125^\circ C$	-	-	1000	
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	2.5	-	4.5	V
Static drain - source on - state resistance	$R_{DS(on)}^{*6}$	$V_{GS} = 10V, I_D = 3A$ $T_j = 25^\circ C$	-	0.9	1.2	Ω
		$T_j = 125^\circ C$	-	1.88	-	
Gate input resistance	R_G	f = 1MHz, open drain	-	8.9	-	Ω

●Electrical characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Transconductance	g_{fs}^{*6}	$V_{DS} = 10\text{V}, I_D = 3.0\text{A}$	1.7	3.9	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$	-	460	-	pF
Output capacitance	C_{oss}	$V_{DS} = 25\text{V}$	-	370	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	24	-	
Effective output capacitance, energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$ $V_{DS} = 0\text{V to } 480\text{V}$	-	22.2	-	pF
Effective output capacitance, time related	$C_{o(tr)}$		-	67.5	-	
Turn - on delay time	$t_{d(on)}^{*6}$	$V_{DD} \approx 300\text{V}, V_{GS} = 10\text{V}$	-	22	-	ns
Rise time	t_r^{*6}	$I_D = 3\text{A}$	-	36	-	
Turn - off delay time	$t_{d(off)}^{*6}$	$R_L = 100\Omega$	-	50	100	
Fall time	t_f^{*6}	$R_G = 10\Omega$	-	35	70	

●Gate Charge characteristics($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*6}	$V_{DD} \approx 300\text{V}$	-	15	-	nC
Gate - Source charge	Q_{gs}^{*6}	$I_D = 6\text{A}$	-	4	-	
Gate - Drain charge	Q_{gd}^{*6}	$V_{GS} = 10\text{V}$	-	7	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} \approx 300\text{V}, I_D = 6\text{A}$	-	5.9	-	V

*1 Limited only by maximum temperature allowed.

*2 $P_W \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 $L \approx 500\mu\text{H}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, starting $T_j = 25^\circ\text{C}$

*4 $L \approx 500\mu\text{H}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, starting $T_j = 25^\circ\text{C}$, $f = 10\text{kHz}$

*5 Reference measurement circuits Fig.5-1.

*6 Pulsed

●Body diode electrical characteristics (Source-Drain)($T_a = 25^\circ\text{C}$)

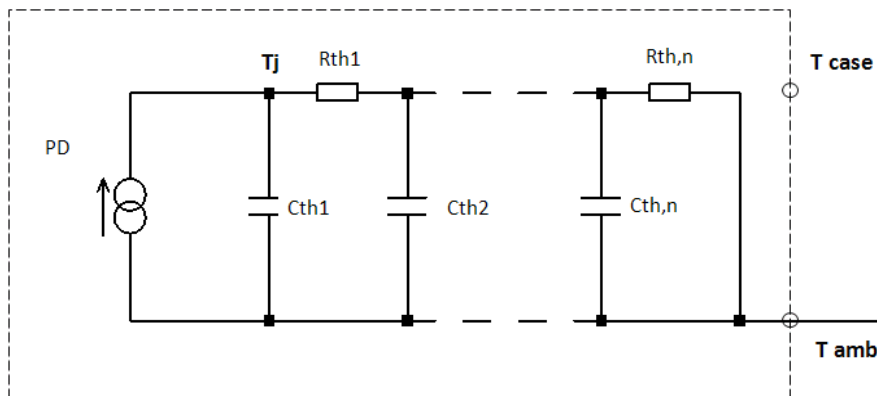
Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_S^{*1}	$T_c = 25^\circ\text{C}$	-	-	6	A
Inverse diode direct current, pulsed	I_{SM}^{*2}		-	-	24	A
Forward voltage	V_{SD}^{*6}	$V_{GS} = 0\text{V}, I_S = 6\text{A}$	-	-	1.5	V
Reverse recovery time	t_{rr}^{*6}	$I_S = 6\text{A}$ $di/dt = 100\text{A}/\mu\text{s}$	-	270	-	ns
Reverse recovery charge	Q_{rr}^{*6}		-	1.9	-	μC
Peak reverse recovery current	I_{rrm}^{*6}		-	13	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt	$T_j = 25^\circ\text{C}$	-	150	-	$\text{A}/\mu\text{s}$

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R_{th1}	1.08	K/W
R_{th2}	2.21	
R_{th3}	21.4	
R_{th4}	43	

Symbol	Value	Unit
C_{th1}	0.00236	Ws/K
C_{th2}	0.0126	
C_{th3}	0.153	
C_{th4}	1.25	

* Mounted on 25mm x 25mm x 0.8mm glass epoxy board with both side copper.



●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

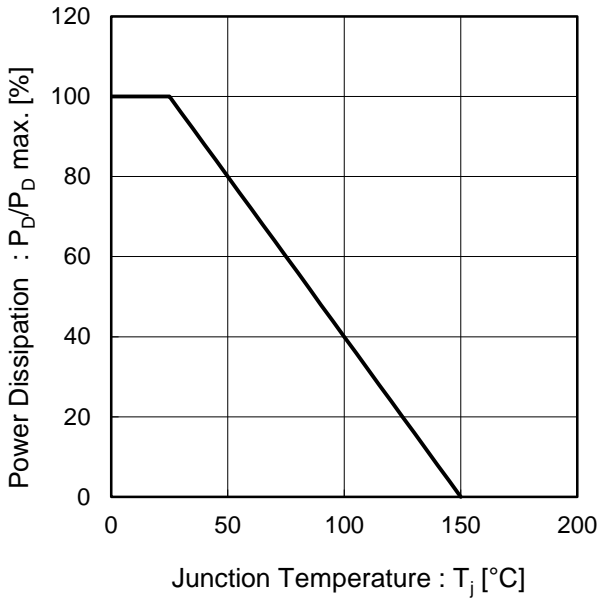


Fig.2 Maximum Safe Operating Area

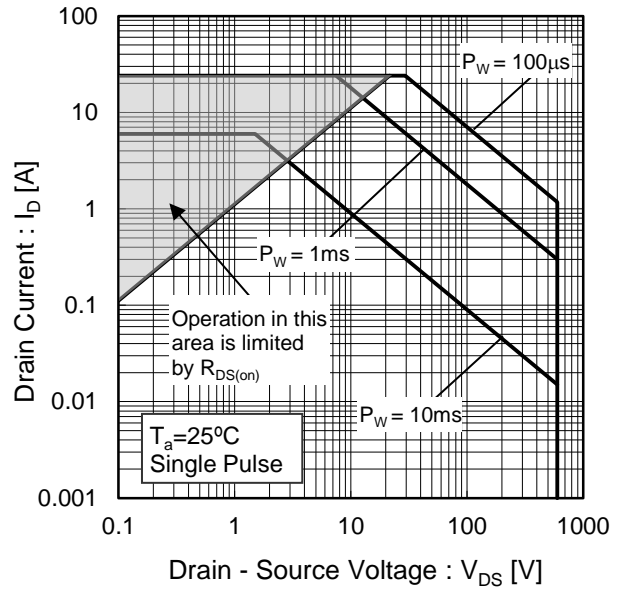
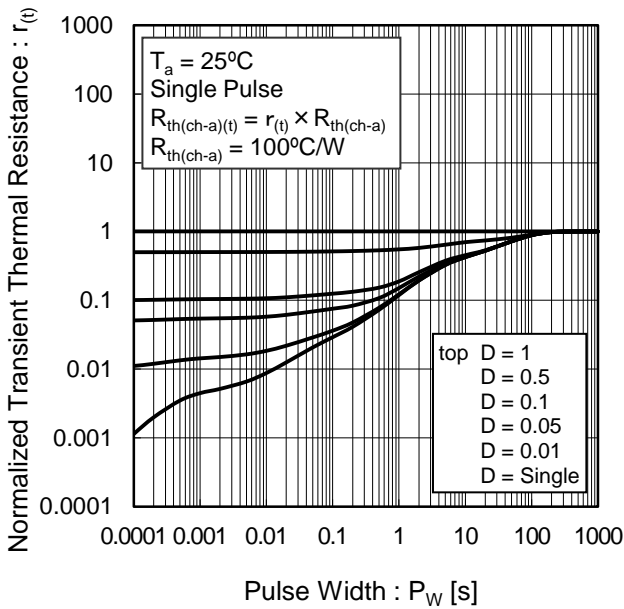


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Avalanche Current vs Inductive Load

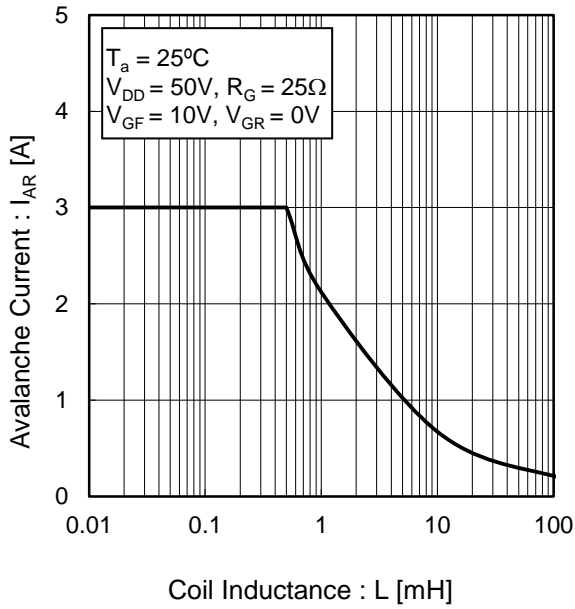


Fig.5 Avalanche Power Losses

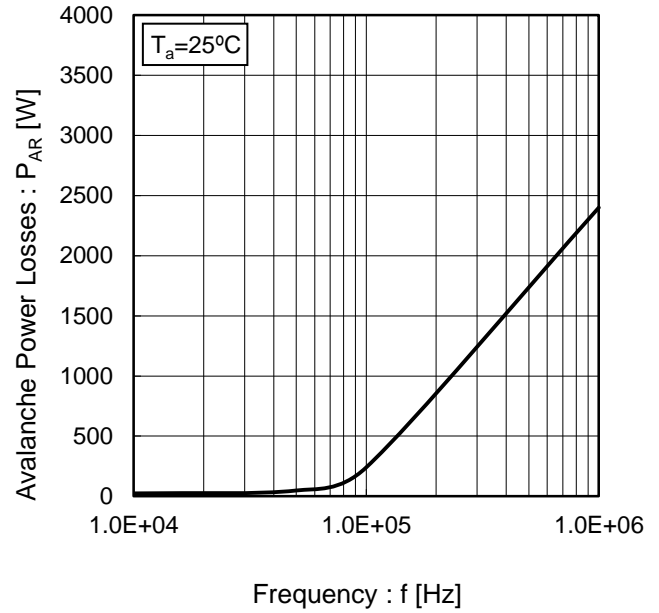
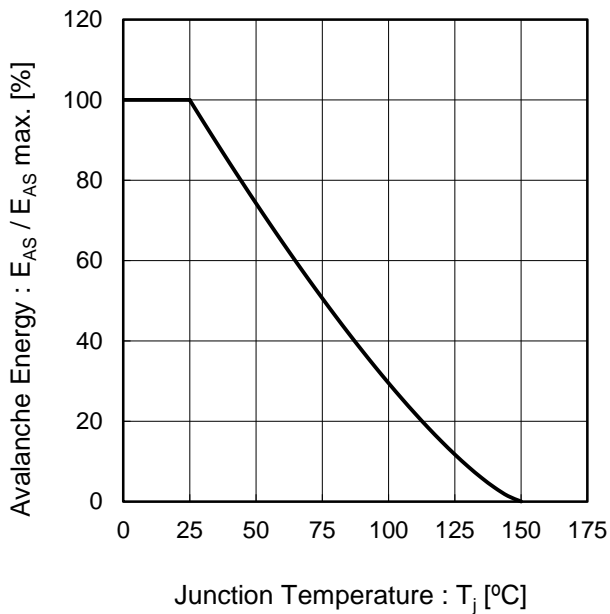


Fig.6 Avalanche Energy Derating Curve vs Junction Temperature



●Electrical characteristic curves

Fig.7 Typical Output Characteristics(I)

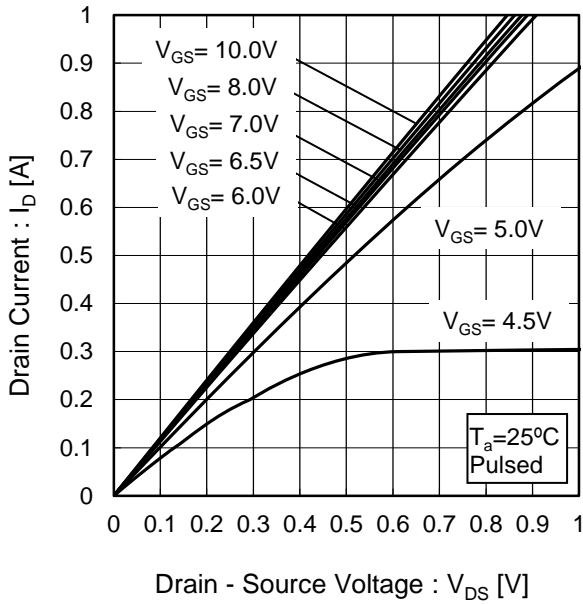


Fig.8 Typical Output Characteristics(II)

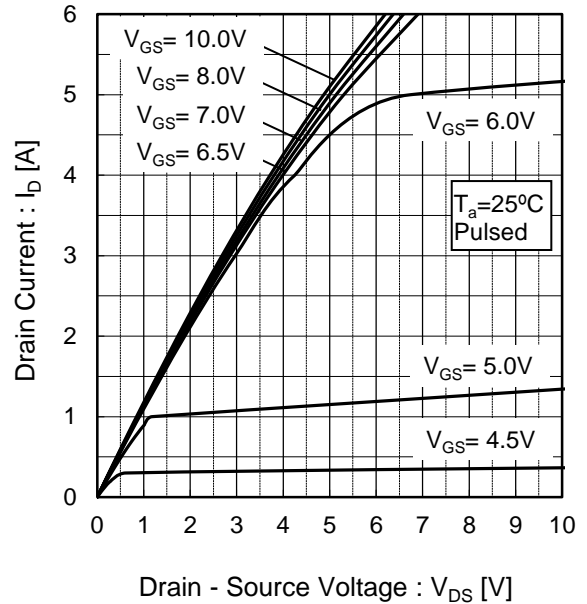


Fig.9 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(I)

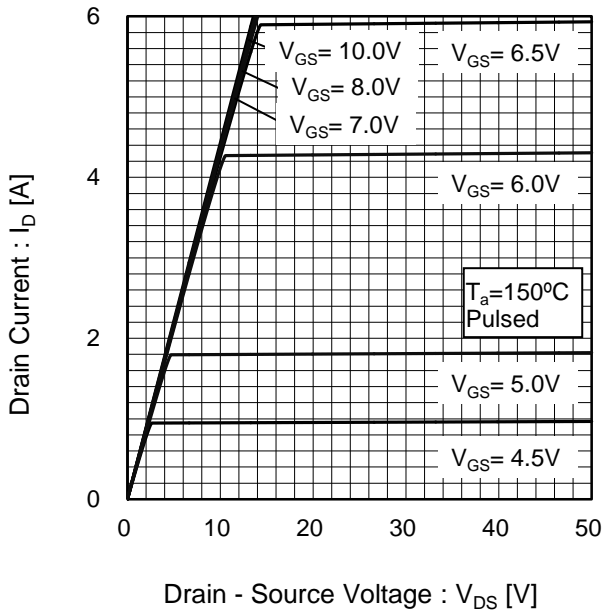
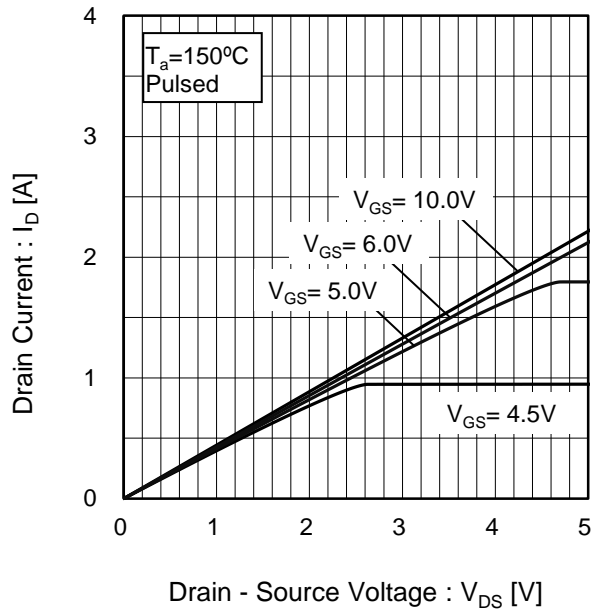


Fig.10 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.11 Breakdown Voltage vs. Junction Temperature

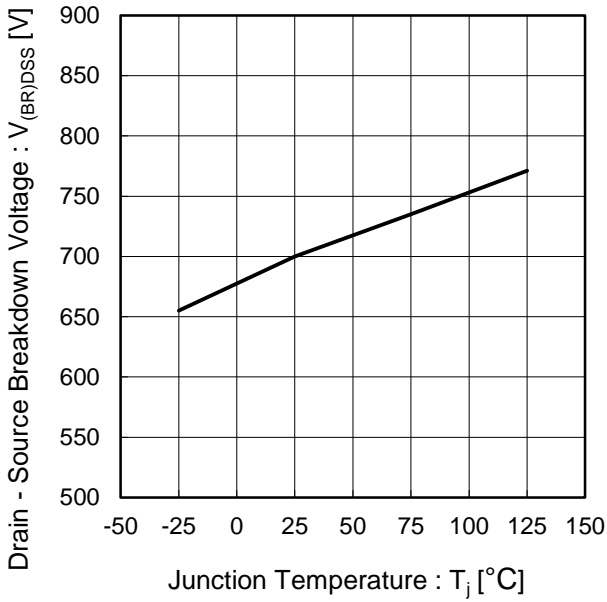


Fig.12 Typical Transfer Characteristics

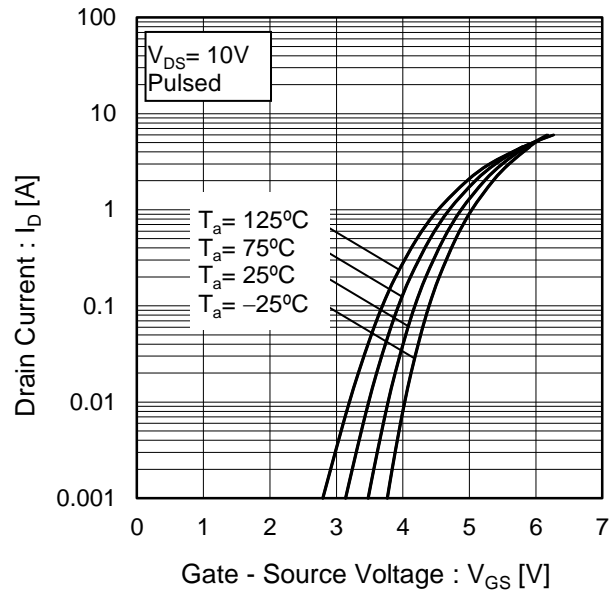


Fig.13 Gate Threshold Voltage vs. Junction Temperature

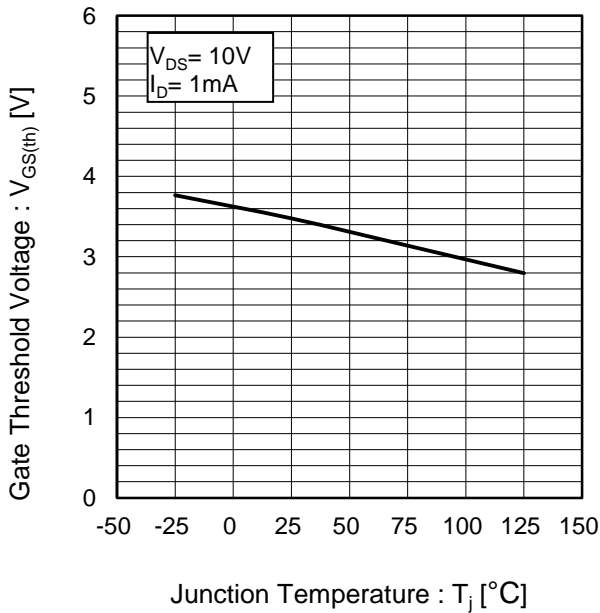
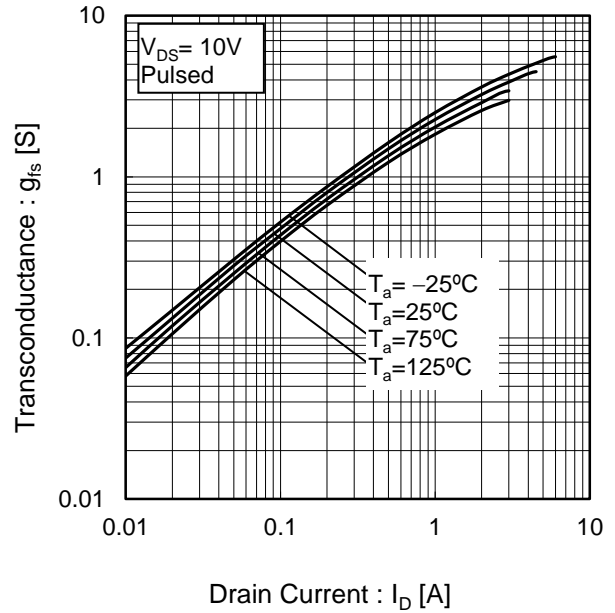


Fig.14 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage

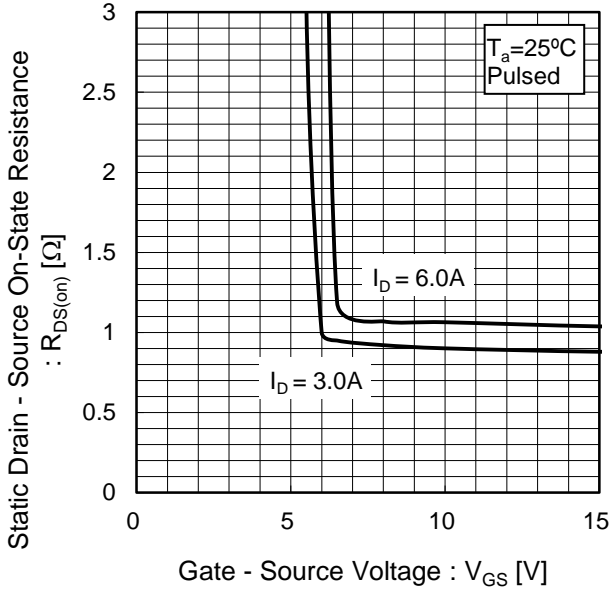


Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature

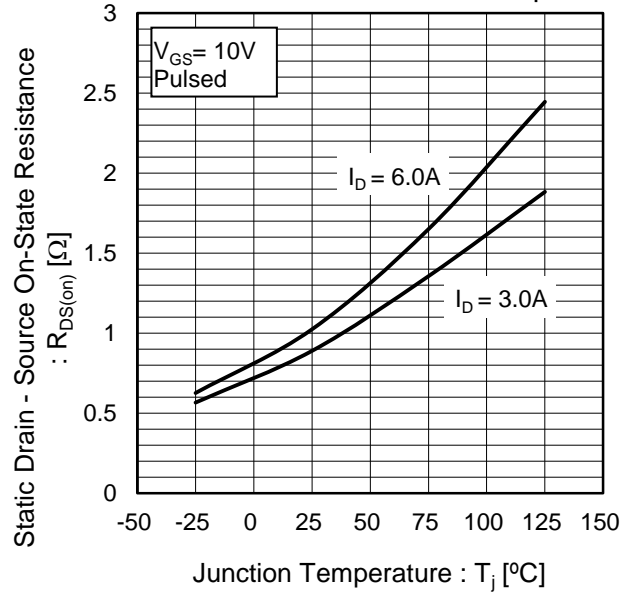
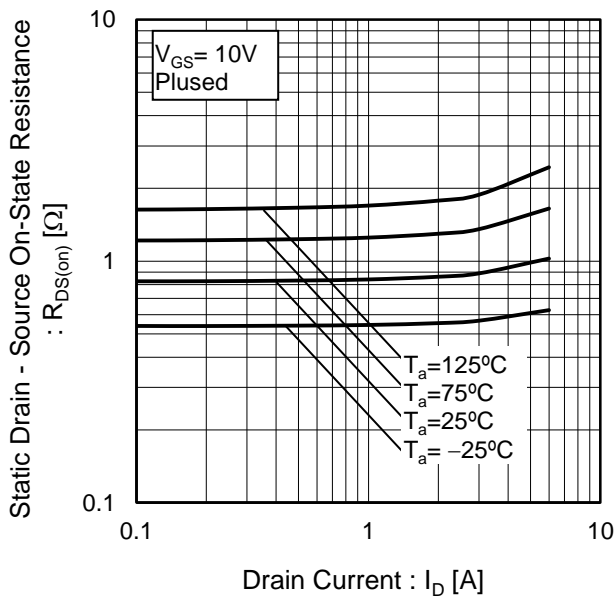


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current



●Electrical characteristic curves

Fig.18 Typical Capacitance vs. Drain - Source Voltage

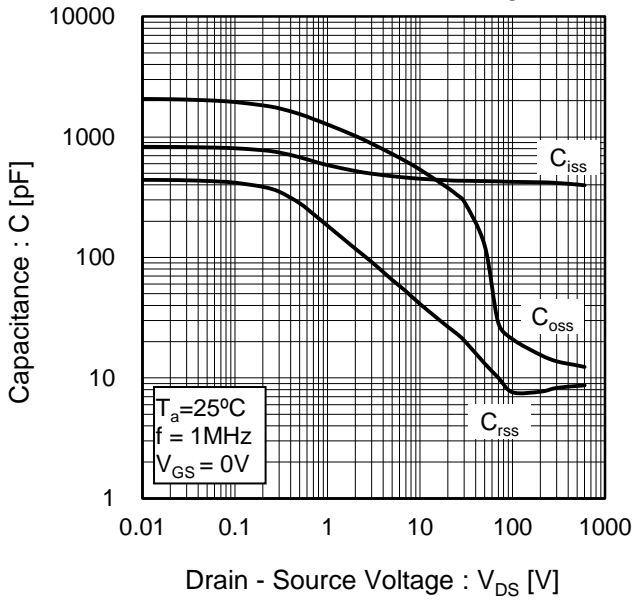


Fig.19 Coss Stored Energy

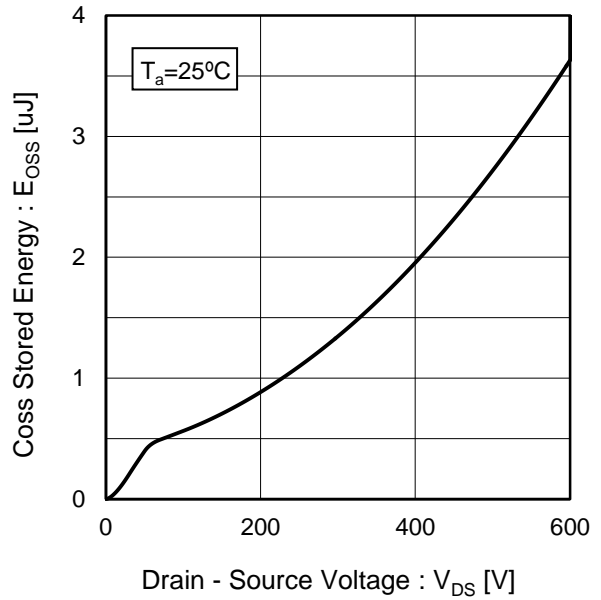


Fig.20 Switching Characteristics

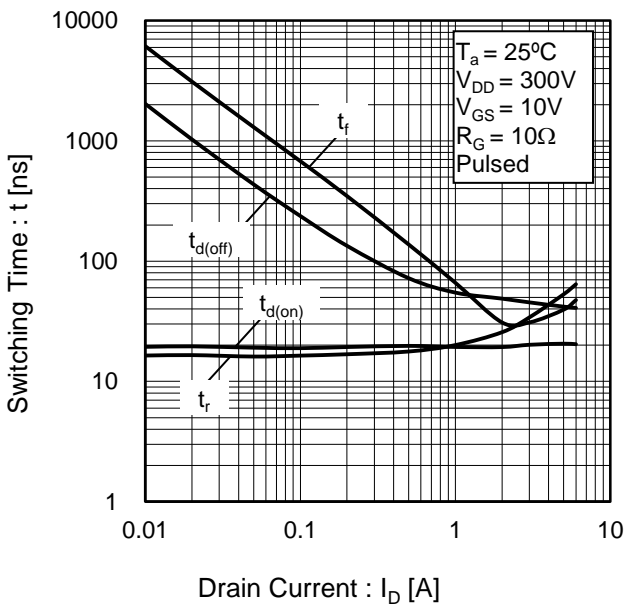
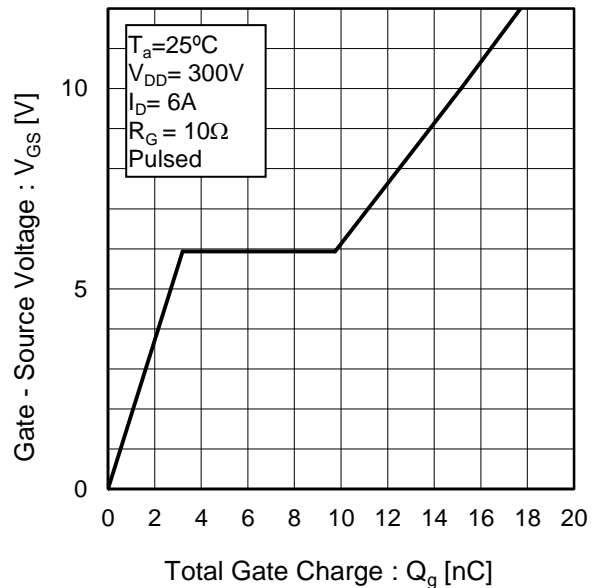


Fig.21 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

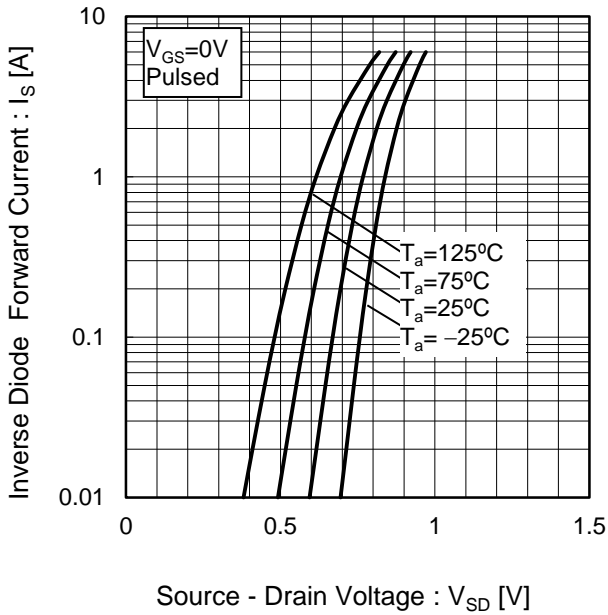
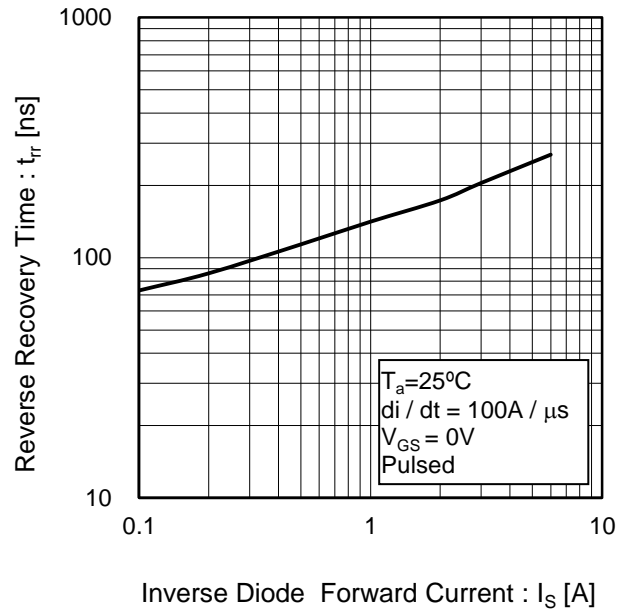


Fig.23 Reverse Recovery Time vs. Inverse Diode Forward Current



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

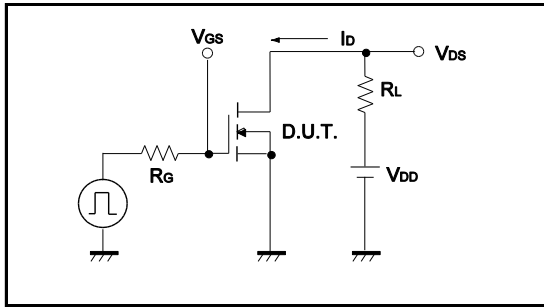


Fig.1-2 Switching Waveforms

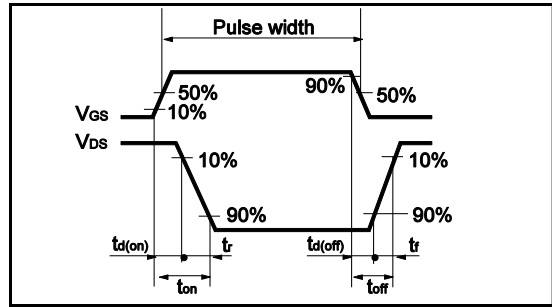


Fig.2-1 Gate Charge Measurement Circuit

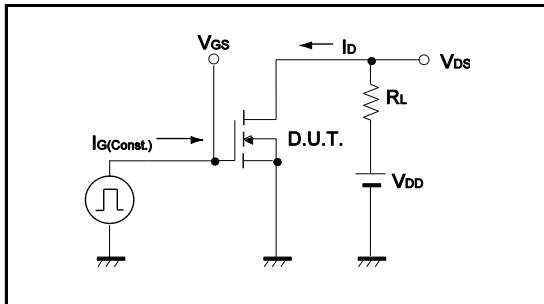


Fig.2-2 Gate Charge Waveform

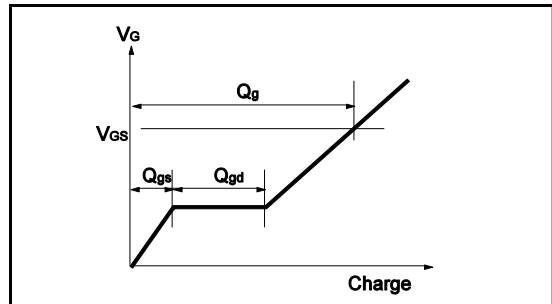


Fig.3-1 Avalanche Measurement Circuit

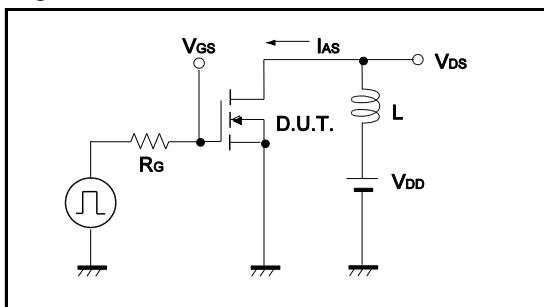


Fig.3-2 Avalanche Waveform

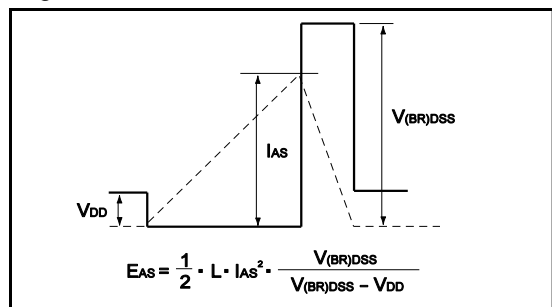


Fig.4-1 dv/dt Measurement Circuit

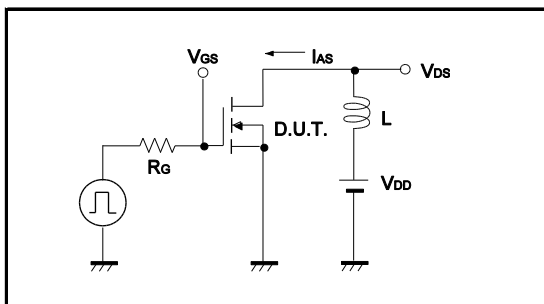


Fig.4-2 dv/dt Waveform

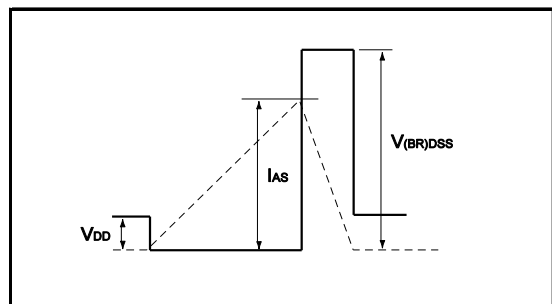


Fig.5-1 di/dt Measurement Circuit

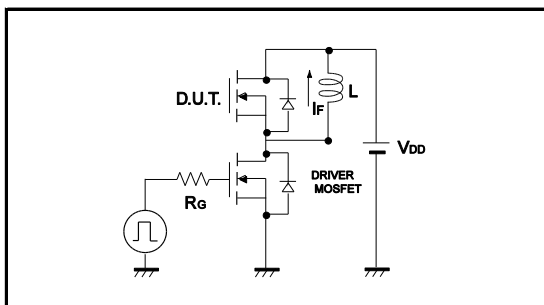
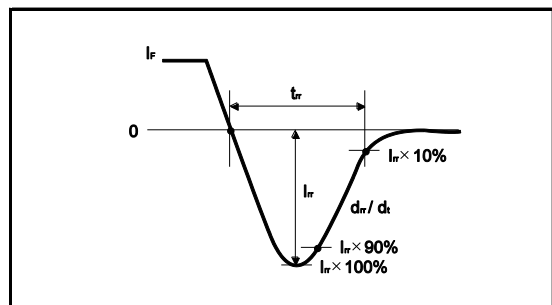
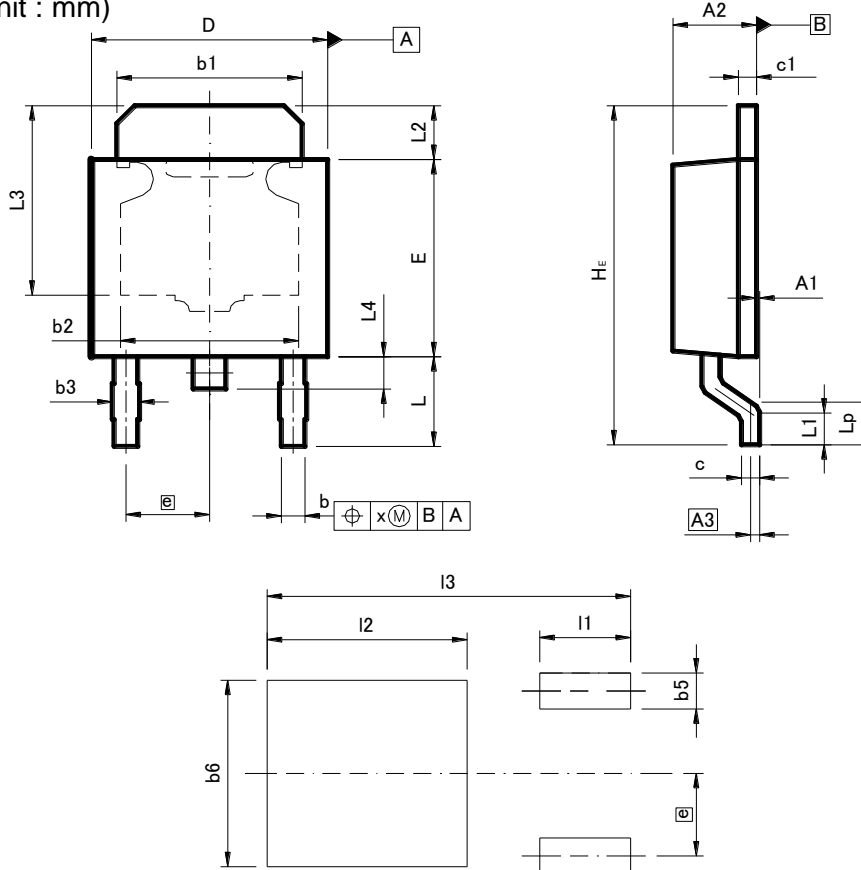


Fig.5-2 di/dt Waveform



●Dimensions (Unit : mm)

CPT3



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A1	0.00	0.15	0.000	0.006
A2	2.20	2.50	0.087	0.098
A3	0.25		0.010	
b	0.55	0.75	0.022	0.030
b1	5.00	5.30	0.197	0.209
b2	5.00		0.197	
b3	0.75		0.030	
c	0.40	0.60	0.016	0.024
c1	0.40	0.60	0.016	0.024
D	6.30	6.70	0.248	0.264
E	5.40	5.80	0.213	0.228
e	2.30		0.091	
HE	9.00	10.00	0.354	0.394
L	2.20	2.80	0.087	0.110
L1	0.80	1.40	0.031	0.055
L2	1.20	1.80	0.047	0.071
L3	5.30		0.209	
L4	0.90		0.035	
Lp	1.00	1.60	0.039	0.063
x	-	0.25	-	0.010

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b5	-	1.00	-	0.04
b6	-	5.20	-	0.205
l1	-	2.50	-	0.098
l2	-	5.50	-	0.217
l3	-	10.00	-	0.394

Dimension in mm / inches

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